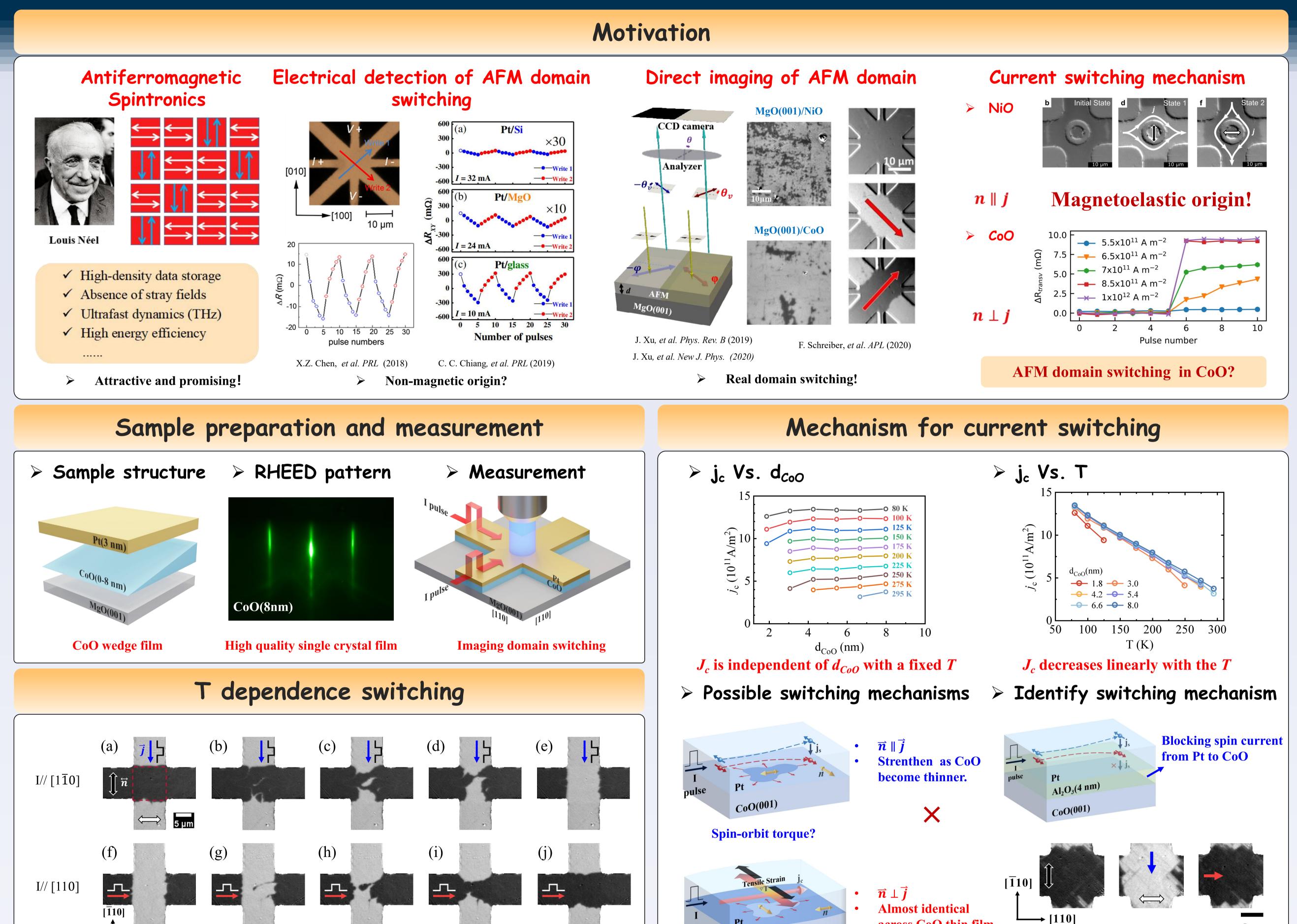
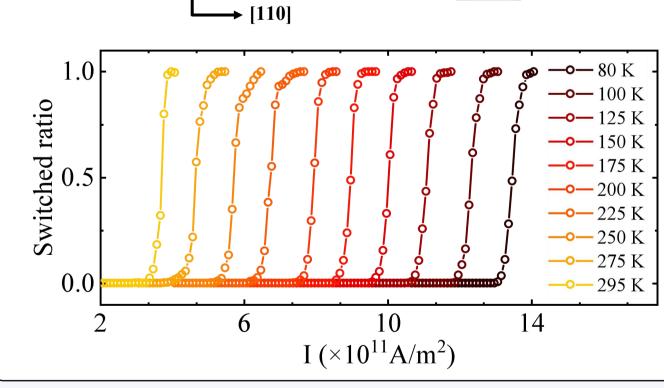


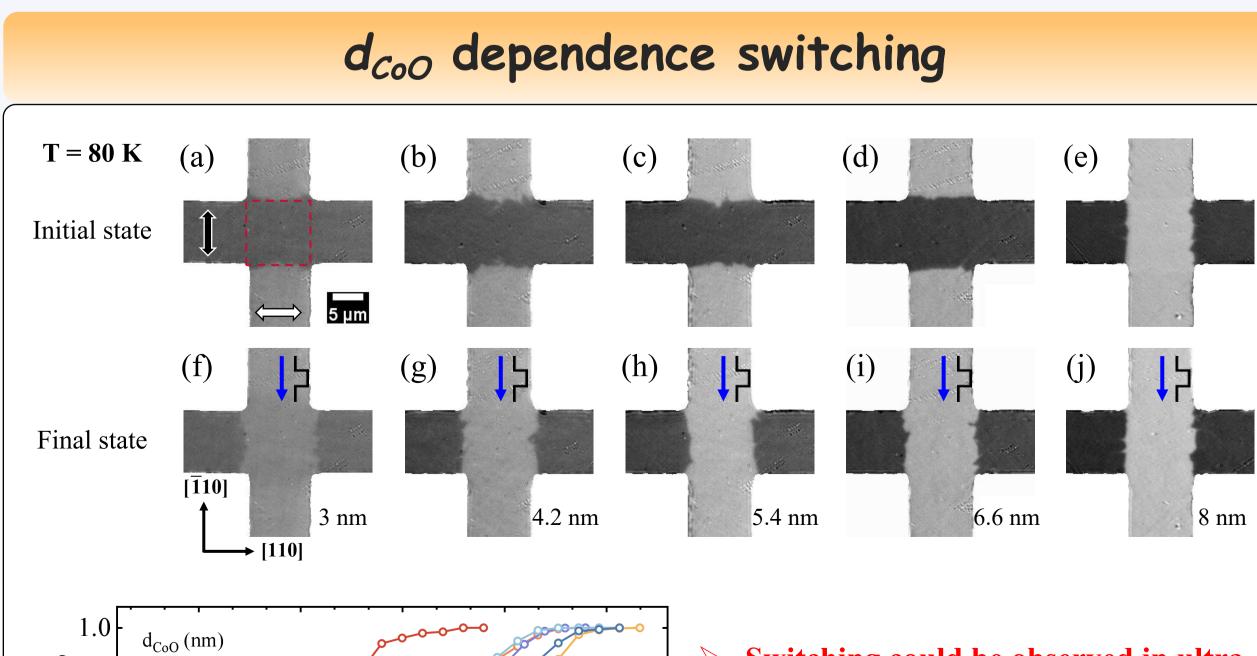
Current-density-modulated Antiferromagnetic Domain Switching in CoO(001)/Pt Bilayer Revealed by Optical Imaging Tong Wu¹, Haoran Chen¹, Jia Xu¹, Yizheng Wu¹

¹ Physics department, Fudan University, Shanghai, China

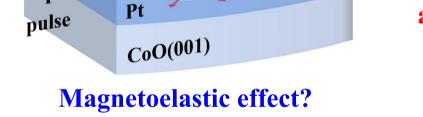




- **Reversible and clear AFM domain** switching.
- > AFM domain switching could be realized within a wide range of temperature for 8 nm CoO.



- Switching could be observed in ultra-thin CoO film.
- Switching polarity are the same for



White domain ratio (%) 0 00 001 001

y [110]

└→ x [110]

across CoO thin film.

5 um Similar reversible switching behaviour

Magnetoelastic effect dominant switching!

 $\mathbf{Q} n \perp \mathbf{j}$

n || j

 $12 \times 10^{11} \text{A/m}^2$

10

12

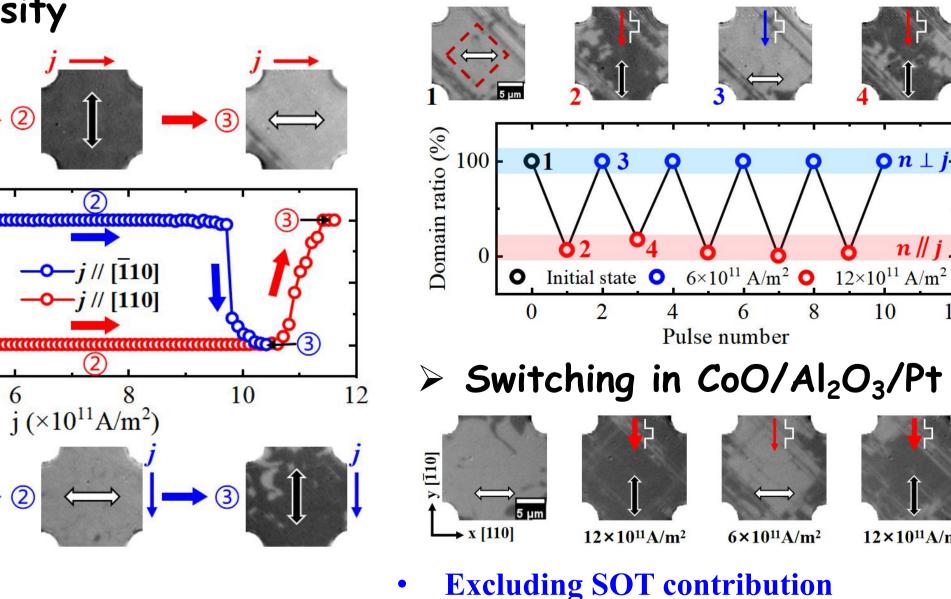
Current-density-modulated switching

> Switching curve with increasing current density

6

Switching polarity changes at higher *j*

> Reversible switching

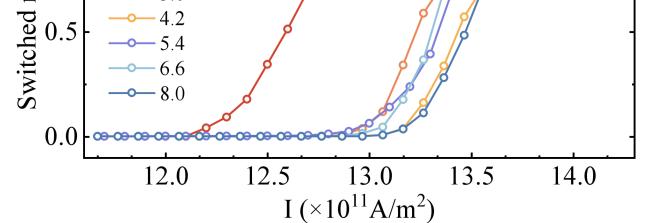


Different strain distribution at higher *j*

Summary

Imaging current switching of AFM domains in CoO/Pt

 \succ AFM domain switching was observed with different T d_{CoO} .



ratio

———1.8

---3.0

---4.2

—•— 5.4

